



#### 60V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>C</sub> = +25°C
-60V	$50m\Omega$ @ $V_{GS} = -10V$	-26A
	70mΩ @ V <sub>GS</sub> = -4.5V	-22A

## **Description and Applications**

This new generation 60V P-Channel Enhancement Mode MOSFET is designed to minimize  $R_{DS(ON)}$  and yet maintain superior switching performance. This device is ideal for use in Notebook battery power management and loadswitch.

- Notebook Battery Power Management
- DC-DC Converters
- Loadswitch

#### **Features and Benefits**

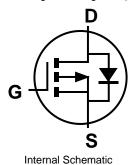
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile Ideal for Thin Applications</li>
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

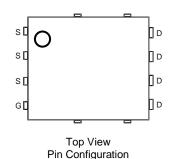
#### **Mechanical Data**

- Case: PowerDI<sup>®</sup> 5060-8
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208 <sup>(3)</sup>
- Weight: 0.097 grams (Approximate)



Top View Bottom View





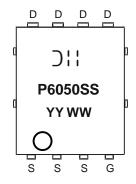
**Ordering Information** (Note 4)

Part Number	Case	Packaging
DMP6050SPS-13	PowerDI5060-8	2500 / Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# Marking Information



D!! = Manufacturer's Marking
P6050SS = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 18 = 2018)
WW = Week Code (01 to 53)



# **Maximum Ratings** $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-60	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	-5.7 -4.5	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-45	Α
Maximum Continuous Body Diode Forward Current (Note 6)			Is	-2.4	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I <sub>SM</sub>	-45	Α
Avalanche Current (Note 8) L = 0.1mH			I <sub>AS</sub>	-25	Α
Repetitive Avalanche Energy (Note 8) L = 0.1mH			Eas	32	mJ

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	1.3	W
Thermal Resistance, Junction to Ambient @ T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	95	°C/W
Power Dissipation (Note 6)	P <sub>D</sub>	2.4	W
Thermal Resistance, Junction to Ambient @ T <sub>A</sub> = +25°C (Note 6)	R <sub>θJA</sub>	52	°C/W
Thermal Resistance, Junction to Case @ T <sub>C</sub> = +25°C (Note 7)	R <sub>0JC</sub>	2.4	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-60	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1	μA	$V_{DS} = -60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)						•	
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.0	_	-3.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
Static Drain-Source On-Resistance	В	_	43	50	mΩ	$V_{GS} = -10V, I_D = -5A$	
Static Dialii-Source On-Resistance	R <sub>DS(ON)</sub>	_	53	70	11122	$V_{GS} = -4.5V, I_D = -4A$	
Diode Forward Voltage	V <sub>SD</sub>	_	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A	
DYNAMIC CHARACTERISTICS (Note 10)	•	•	•		•	•	
Input Capacitance	C <sub>iss</sub>	_	2163	_	pF	.,	
Output Capacitance	Coss	_	88	_	pF	$V_{DS} = -30V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	58	_	pF		
Gate Resistance	Rg	_	13	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = -10V)	Qg	_	30	_	nC		
Total Gate Charge (V <sub>GS</sub> = -4.5V)	Qg	_	14	_	nC	), 20V I 5A	
Gate-Source Charge	Qgs	_	5	_	nC	$V_{DS} = -30V, I_{D} = -5A$	
Gate-Drain Charge	Q <sub>gd</sub>	_	4.6	<u> </u>	nC	1	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.7	_	ns		
Turn-On Rise Time	t <sub>R</sub>	_	2.7	_	ns	$V_{GS} = -10V, V_{DS} = -30V,$ $R_G = 3\Omega, I_D = -5A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	73	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	25	_	ns		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	_	18	_	ns	$I_F = -5A$ , di/dt = 100A/ $\mu$ s	
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	_	12	_	nC	$I_F = -5A$ , $di/dt = 100A/\mu s$	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. Notes:

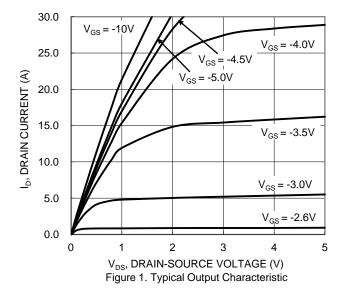
<sup>6.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

<sup>7.</sup> Thermal resistance from junction to soldering point (on the exposed drain pad).

<sup>8.</sup>  $I_{AS}$  and  $E_{AS}$  ratings are based on low frequency and duty cycles to keep  $T_J$  = +25°C. 9. Short duration pulse test used to minimize self-heating effect.

<sup>10.</sup> Guaranteed by design. Not subject to product testing.





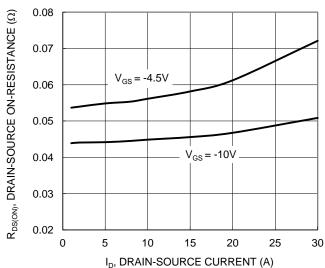


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

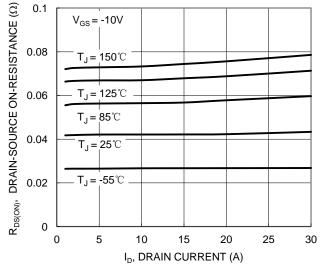
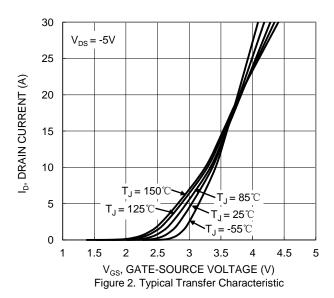
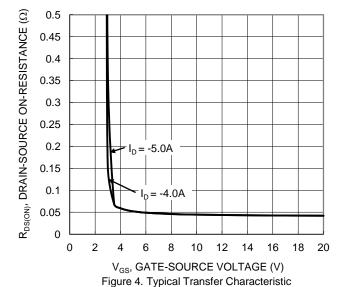


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





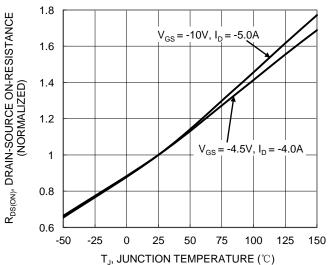


Figure 6. On-Resistance Variation with Junction Temperature



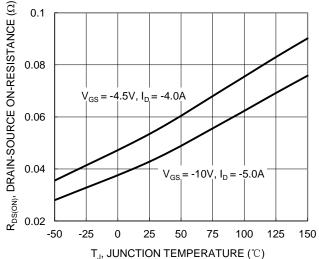
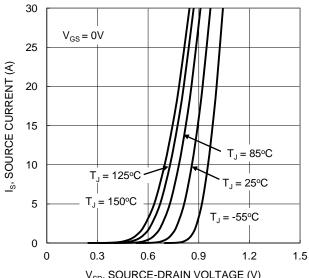


Figure 7. On-Resistance Variation with Junction
Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

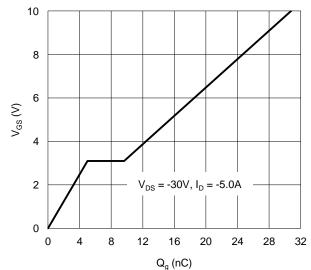


Figure 11. Gate Charge

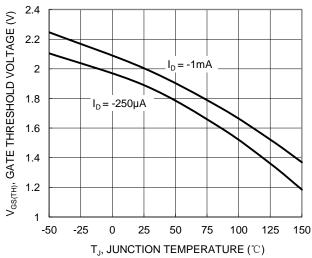
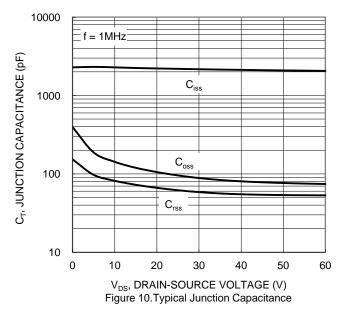


Figure 8. Gate Threshold Variation vs. Junction Temperature



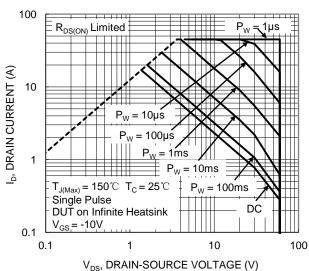


Figure 12. SOA, Safe Operation Area



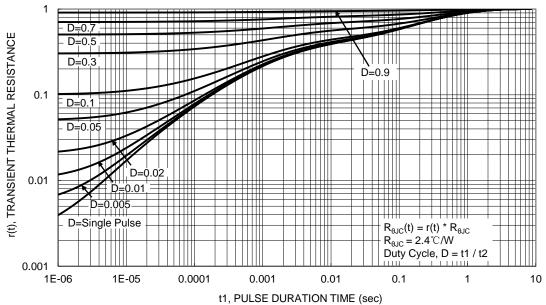


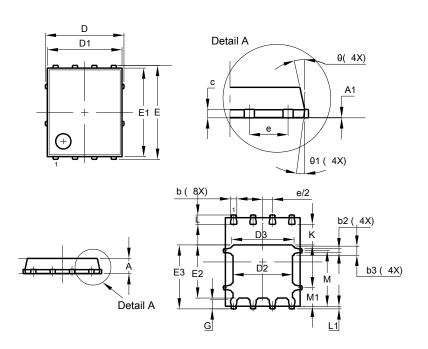
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI5060-8

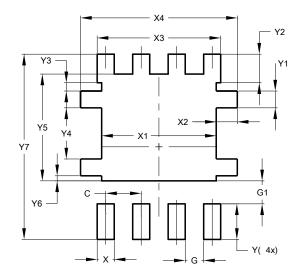


D DI5000.0					
PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	_		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
C D	0.230	0.330	0.277		
	5.15 BSC				
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90	4.30	4.10		
Е	•	6.15 BSC	;		
E1	5.60	6.00	5.80		
E2	3.28	3.68	3.48		
E3	3.99	4.39	4.19		
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	-	-		
L	0.51	0.71	0.61		
L1	0.100	0.200	0.175		
M	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### PowerDI5060-8



Dimensions	Value (in mm)			
С	1.270			
G	0.660			
G1	0.820			
Χ	0.610			
X1	4.100			
X2	0.755			
Х3	4.420			
X4	5.610			
Υ	1.270			
Y1	0.600			
Y2	1.020			
Y3	0.295			
Y4	1.825			
Y5	3.810			
Y6	0.180			
Y7	6.610			



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